

ABSTRACT

The present invention relates to the technical field of integrated circuit chip manufacturing, and in particular to a gas control device. The device comprises a gas intake unit, a filter plate, a diffuser plate, and a gas guide unit. The gas intake unit is formed with an opening for flowing gas to the filter plate, the filter plate is arranged corresponding to the opening, and the diffuser plate is arranged below the filter plate. The gas is vertically blown to the surface of a wafer to be processed after passing through the gas intake unit, the filter plate, and the diffuser plate in sequence. The gas guide unit comprises at least one gas guide plate, and the at least one gas guide plate is arranged at a gas guide port of the gas intake unit. The gas guide plate is added to the gas intake path, the gas guide plate guides the gas, and the partitioned gas flow is blown into the gas intake unit, so that the gas flow velocity blown to all parts on the surface of the wafer is kept uniform.